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## FDS9953A

## **Dual 30V P-Channel PowerTrench® MOSFET**

### **General Description**

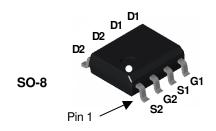
This P-Channel MOSFET is a rugged gate version of Fairchild Semiconductor's advanced PowerTrench process. It has been optimized for power management applications requiring a wide range of gave drive voltage ratings (4.5V-25V).

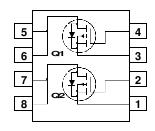
### **Applications**

- Power management
- Load switch
- Battery protection

### Features

- -2.9 A, -30 V  $R_{DS(ON)} = 130 \text{ m}\Omega$  @  $V_{GS} = -10 \text{ V}$   $R_{DS(ON)} = 200 \text{ m}\Omega$  @  $V_{GS} = -4.5 \text{ V}$
- Low gate charge (2.5nC typical)
- Fast switching speed
- High performance trench technology for extremely low R<sub>DS(ON)</sub>
- High power and current handling capability





## Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		-30	V
V <sub>GSS</sub>	Gate-Source Voltage		±25	V
I <sub>D</sub>	Drain Current - Continuous	(Note 1a)	±2.9	А
	- Pulsed		±10	
PD	Power Dissipation for Dual Operation		2	W
	Power Dissipation for Single Operation	(Note 1a)	1.6	
		(Note 1b)	1	
		(Note 1c)	0.9	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range		-55 to +150	°C

### **Thermal Characteristics**

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
R <sub>eJC</sub>	Thermal Resistance, Junction-to-Case	(Note 1)	40	°C/W

## **Package Marking and Ordering Information**

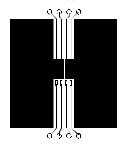
Device Marking Device		Reel Size	Tape width	Quantity	
FDS9953A FDS9953A		13"	12mm	2500 units	

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics		I.		I	ı
BV <sub>DSS</sub>	Drain–Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-30			V
<u>ΔBV<sub>DSS</sub></u> ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$ , Referenced to 25°C		-23		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = -24 \text{ V},  V_{GS} = 0 \text{ V}$			-2	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage, Forward	$V_{GS} = -25 \text{ V},  V_{DS} = 0 \text{ V}$			-100	nA
I <sub>GSSR</sub>	Gate-Body Leakage, Reverse	$V_{GS} = 25 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
On Chara	acteristics (Note 2)		1		ı	I
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$	-1	-1.8	-3.0	V
$\Delta V_{GS(th)} \over \Delta T_{J}$	Gate Threshold Voltage Temperature Coefficient	$I_D$ = –250 μA, Referenced to 25°C		4		mV/°C
R <sub>DS(on)</sub>	Static Drain—Source On—Resistance	$\begin{split} V_{GS} = & -10 \text{ V},  l_D = -1 \text{ A} \\ V_{GS} = & -10 \text{ V},  l_D = -1 \text{ A},  T_J = 125^{\circ}\text{C} \\ V_{GS} = & -4.5 \text{ V},  l_D = -0.5 \text{ A} \\ V_{GS} = & -4.5 \text{ V},  l_D = -0.5 \text{ A},  T_J = 125^{\circ}\text{C} \end{split}$		95 137 142 202	130 200 200 310	mΩ
J On State [	On–State Drain Current	$V_{GS} = -4.5 \text{ V}, I_D = -0.5 \text{ A}, T_J = 125^{\circ}\text{C}$ $V_{GS} = -10 \text{ V}, V_{DS} = -5 \text{ V}$	<b>-</b> 5			Α
I <sub>D(on)</sub>	On-State Drain Guirent	$V_{GS} = -4.5 \text{ V},  V_{DS} = -5 \text{ V}$	-1.5			
<b>g</b> FS	Forward Transconductance	$V_{DS} = -15 \text{ V}, \qquad I_{D} = -1 \text{ A}$		4		S
Dynamic	Characteristics					
Ciss	Input Capacitance	$V_{DS} = -15 \text{ V},  V_{GS} = 0 \text{ V},$		185		рF
Coss	Output Capacitance	f = 1.0 MHz		56		pF
C <sub>rss</sub>	Reverse Transfer Capacitance	7 I = 1.0 IVITIZ		26		pF
Switchin	g Characteristics (Note 2)					
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = -15 \text{ V}, \qquad I_D = -1 \text{ A},$		4.5	9	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = -10 \text{ V}, \qquad R_{GEN} = 6 \Omega$		13	23	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			11	20	ns
t <sub>f</sub>	Turn-Off Fall Time			2	4	ns
Qg	Total Gate Charge	$V_{DS} = -5 V$ , $I_D = -1 A$ ,		2.5	3.5	nC
Q <sub>gs</sub>	Gate-Source Charge	$V_{GS} = -10 \text{ V}$		0.8		nC
Q <sub>gd</sub>	Gate-Drain Charge			0.9		nC
Drain-Sc	ource Diode Characteristics	and Maximum Ratings	I.			ı
ls	Maximum Continuous Drain-Source				-1.2	Α
V <sub>SD</sub>	Drain–Source Diode Forward Voltage	$V_{GS} = 0 \text{ V},  I_S = -1.3 \text{ A}  \text{(Note 2)}$		-0.8	1.3	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>F</sub> = -1.25A, dI <sub>F</sub> /dt = 100A/µs		17	100	nS

## **Typical Characteristics**

#### Notes:

 R<sub>BLA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>BUC</sub> is guaranteed by design while R<sub>BCA</sub> is determined by the user's board design.



78°C/W when mounted on a 0.5in² pad of 2 oz copper



125°C/W when mounted on a 0.02 in<sup>2</sup> pad of 2 oz copper



135°C/W when mounted on a minimum pad.

Scale 1:1 on letter size paper

2. Pulse Test: Pulse Width  $< 300 \mu s$ , Duty Cycle < 2.0%

## **Typical Characteristics**

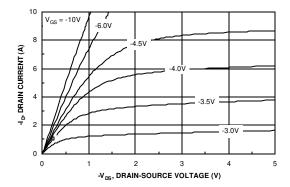


Figure 1. On-Region Characteristics.

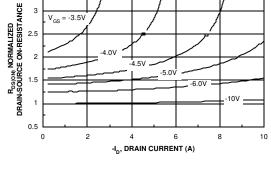


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

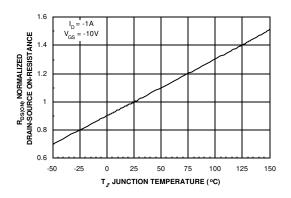


Figure 3. On-Resistance Variation with Temperature.

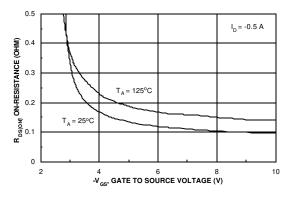


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

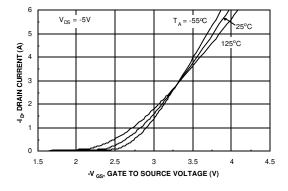


Figure 5. Transfer Characteristics.

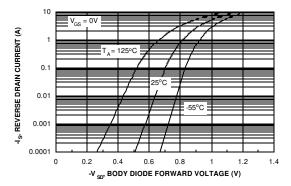
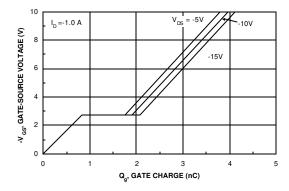


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

## **Typical Characteristics**



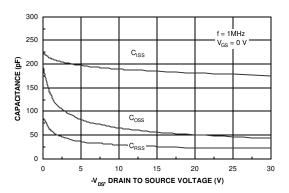
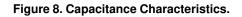
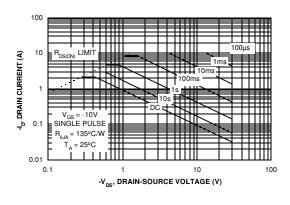


Figure 7. Gate Charge Characteristics.





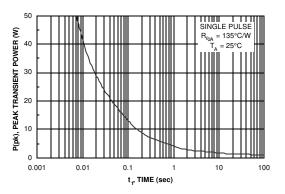


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

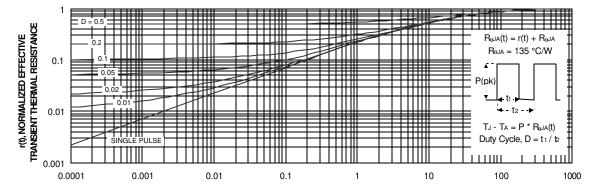


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

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